

**【Document】 ABSTRACT OF THE DISCLOSURE****【ABSTRACT】**

**【Problem】** To provide a semiconductor optical device having a temperature characteristic superior to those of InGaAsP/InP semiconductor optical devices.

**【 Means 】** This semiconductor light-emitting device 1 comprises a first conductivity type semiconductor region, an active layer, a second conductivity type semiconductor layer and current block semiconductor region. The first conductivity type semiconductor region is provided on a surface made of GaAs semiconductor. The active layer is provided on the first conductivity type semiconductor region. The active layer has a pair of side surfaces. The second conductivity type semiconductor layer is provided on the active layer. The second conductivity type semiconductor layer has a pair of side surfaces. The current block semiconductor region is provided on the side surfaces of the active layer and on the side surfaces of the second conductivity type semiconductor layer. The active layer is made of III-V compound semiconductor including at least nitrogen element as a V group member.

**【Representative Drawing】** Fig. 1